

IR2184/IR21844

HIGH AND LOW SIDE DRIVER

Features

- Floating channel designed for bootstrap operation
Fully operational to +600V
Tolerant to negative transient voltage
dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 5V Schmitt triggered input logic
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- High side output in phase with IN input
- Logic and power ground +/- 5V offset.
- Internal 500ns dead-time, and programmable up to 5 μ s with one external R_{DT} resistor (IR21844)
- Lower di/dt gate driver for better noise immunity
- Shut down input turns off both channels.

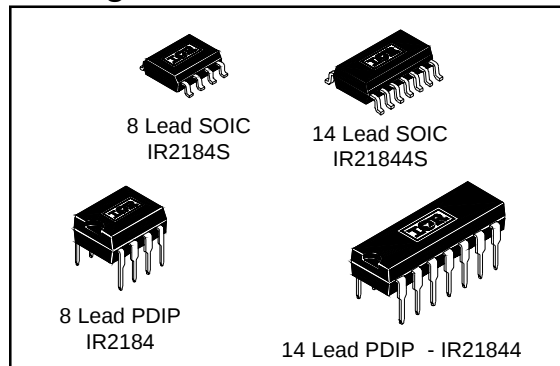
Description

The IR2184/IR21844 are high voltage, high speed power MOSFET and IGBT drivers with dependant high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

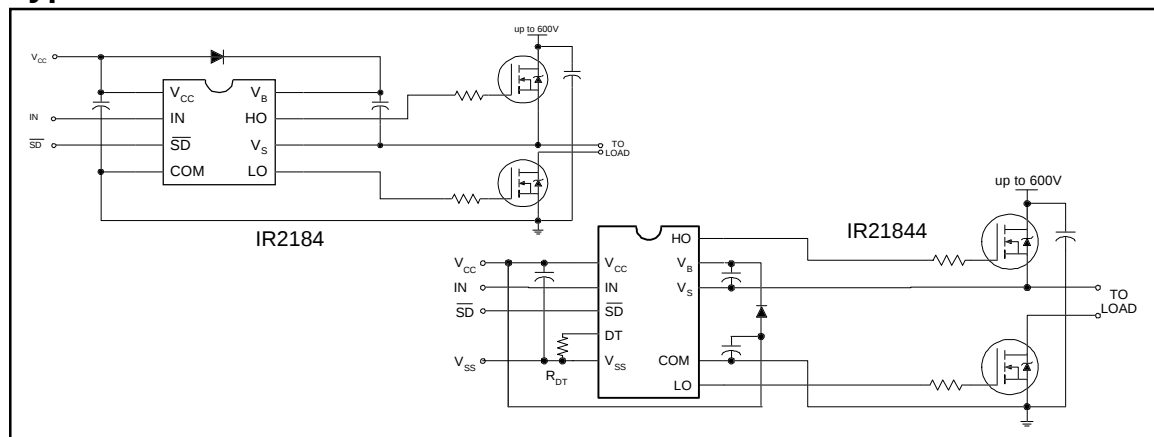
Product Summary

V _{OFFSET}	600V max.
I _O +/-	1.7A / 1.7A
V _{OUT}	10 - 20V
t _{on/off} (typ.)	680 & 180 ns
Deadtime (typ.)	500 ns
	(programmable up to 5 μ s for IR21844)

Packages



Typical Connection



IR2184/IR21844

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Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating absolute voltage	-0.3	625	V	
V _S	High side floating supply offset voltage	V _B - 25	V _B + 0.3		
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3		
V _{CC}	Low side and logic fixed supply voltage	-0.3	25		
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3		
DT	Programmable dead-time pin voltage (IR21844 only)	V _{SS} - 0.3	V _{CC} + 0.3		
V _{IN}	Logic input voltage (IN & $\overline{SD}$)	V _{SS} - 0.3	V _{CC} + 0.3		
V _{SS}	Logic ground (IR21844 only)	V _{CC} - 25	V _{CC} + 0.3		
dV _S /dt	Allowable offset supply voltage transient	—	50	V/ns	
P _D	Package power dissipation @ T _A ≤ +25°C	(8 Lead PDIP)	—	1.0	W
		(8 Lead SOIC)	—	0.625	
		(14 lead PDIP)	—	1.6	
		(14 lead SOIC)	—	1.0	
R _{thJA}	Thermal resistance, junction to ambient	(8 Lead PDIP)	—	125	°C/W
		(8 Lead SOIC)	—	200	
		(14 lead PDIP)	—	75	
		(14 lead SOIC)	—	120	
T _J	Junction temperature	—	150	°C	
T _S	Storage temperature	-50	150		
T _L	Lead temperature (soldering, 10 seconds)	—	300		

Recommended Operating Conditions

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply absolute voltage	V _S + 10	V _S + 20	V
V _S	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	V _S	V _B	
V _{CC}	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	
V _{IN}	Logic input voltage (IN & $\overline{SD}$)	V _{SS}	V _{CC}	
DT	Programmable dead-time pin voltage (IR21844 only)	V _{SS}	V _{CC}	
V _{SS}	Logic ground (IR21844 only)	-5	5	
T _A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}.

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C, DT = V_{SS} unless otherwise specified.

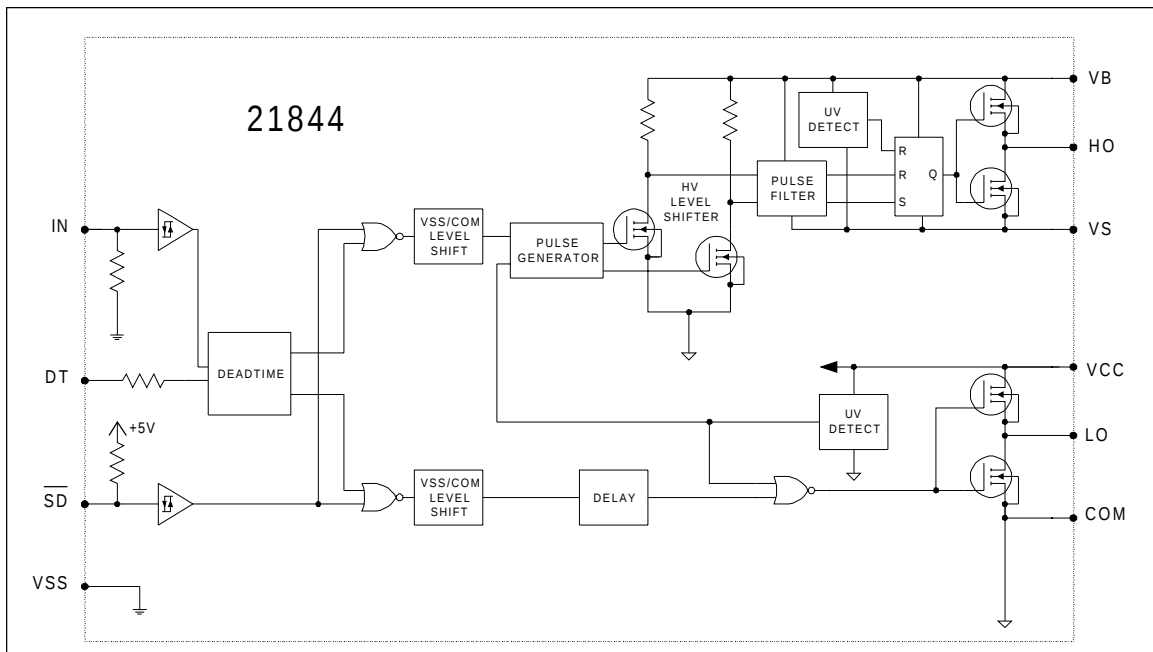
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_{on}	Turn-on propagation delay	—	680	900	nsec	$V_S = 0V$
t_{off}	Turn-off propagation delay	—	170	250		$V_S = 0V$ or 600V
t_{sd}	Shut-down propagation delay	—	180	270		
MT	Delay matching, HS & LS turn-on/off	—	0	—		
t_r	Turn-on rise time	—	40	60		$V_S = 0V$
t_f	Turn-off fall time	—	20	30		$V_S = 0V$
DT	Deadtime: LO turn-off to HO turn-on(DT _{LO-HO})	380	500	620	usec	RDT = 0
	HO turn-off to LO turn-on (DT _{HO-LO})	4	5	6		RDT = 200k (IR21094)
MDT	Deadtime matching = DT _{LO} - HO - DT _{HO-LO}	—	0	60	nsec	RDT=0
		—	0	600		RDT = 200k (IR21094)

Static Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 15V, V_{SS} = COM, DT = V_{SS} and T_A = 25°C unless otherwise specified. The V_{IL} , V_{IH} and I_{IN} parameters are referenced to V_{SS} /COM and are applicable to the respective input leads: IN and SD. The V_O , I_O and R_{on} parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V_{IH}	Logic "1" input voltage for HO & logic "0" for LO	2.7	—	—	V	$V_{CC} = 10V$ to 20V
V_{IL}	Logic "0" input voltage for HO & logic "1" for LO	—	—	0.8		$V_{CC} = 10V$ to 20V
$V_{SD,TH+}$	$\overline{SD}$ input positive going threshold	2.7	—	—		$V_{CC} = 10V$ to 20V
$V_{SD,TH-}$	$\overline{SD}$ input negative going threshold	—	—	0.8		$V_{CC} = 10V$ to 20V
V_{OH}	High level output voltage, $V_{BIAS} - V_O$	—	—	1.2		$I_O = 0A$
V_{OL}	Low level output voltage, V_O	—	—	0.1		$I_O = 0A$
I_{LK}	Offset supply leakage current	—	—	50	μA	$V_B = V_S = 600V$
I_{QBS}	Quiescent V_{BS} supply current	20	60	150		$V_{IN} = 0V$ or 5V
I_{QCC}	Quiescent V_{CC} supply current	0.4	1.0	1.6	mA	$V_{IN} = 0V$ or 5V
I_{IN+}	Logic "1" input bias current	—	5	20	μA	$I_N = 5V$, $\overline{SD} = 0V$
I_{IN-}	Logic "0" input bias current	—	1	2		$I_N = 0V$, $\overline{SD} = 5V$
V_{CCUV+} V_{BSUV+}	V_{CC} and V_{BS} supply undervoltage positive going threshold	8.0	8.9	9.8	V	
V_{CCUV-} V_{BSUV-}	V_{CC} and V_{BS} supply undervoltage negative going threshold	7.4	8.2	9.0		
V_{CCUVH} V_{BSUVH}	Hysteresis	0.3	0.7	—		
I_{O+}	Output high short circuit pulsed current	1.7	2	—	A	$V_O = 0V$, $PW \leq 10 \mu s$
I_{O-}	Output low short circuit pulsed current	1.7	2	—		$V_O = 15V$, $PW \leq 10 \mu s$

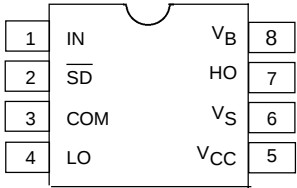
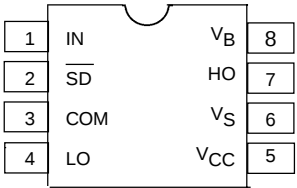
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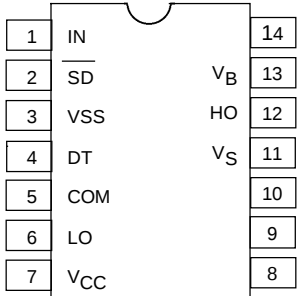
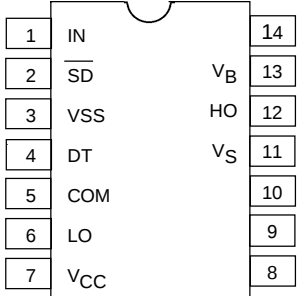
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Lead Definitions

Symbol	Description
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO (referenced to COM for IR2184 and VSS for IR21844)
$\overline{\text{SD}}$	Logic input for shutdown (referenced to COM for IR2184 and VSS for IR21844)
DT	Programmable dead-time lead, referenced to VSS. (IR21844 only)
VSS	Logic Ground (21844 only)
V_B	High side floating supply
HO	High side gate drive output
V_S	High side floating supply return
V_{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

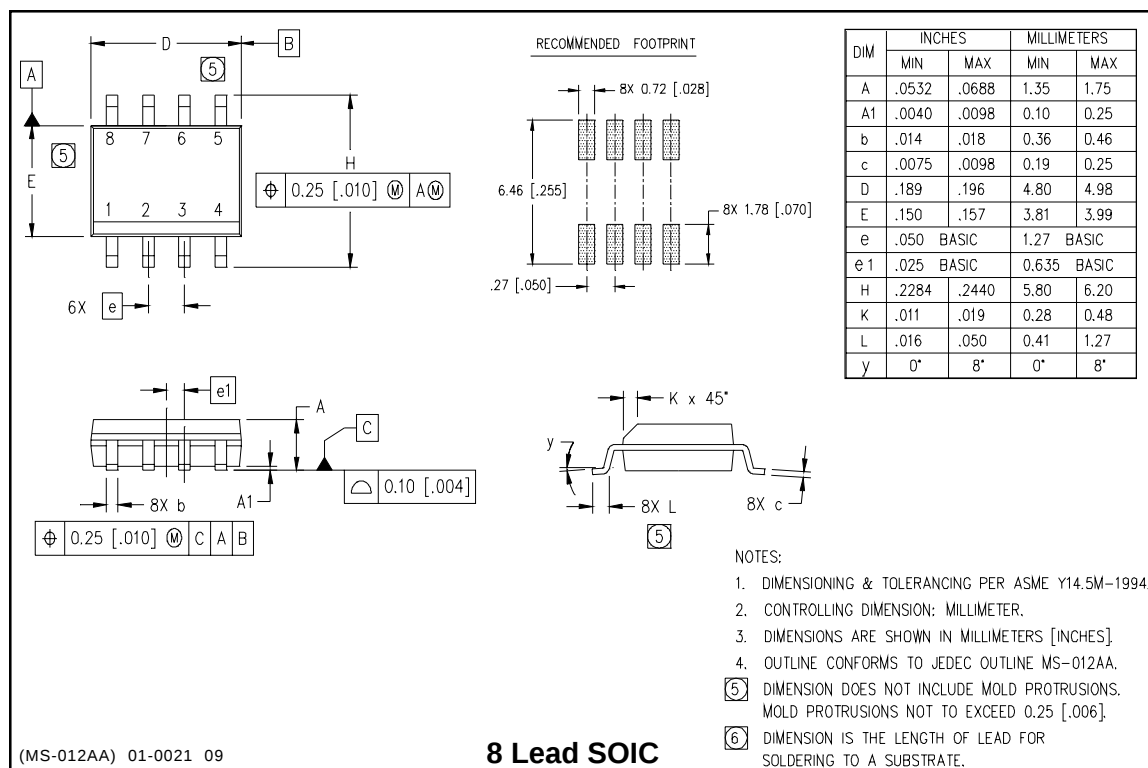
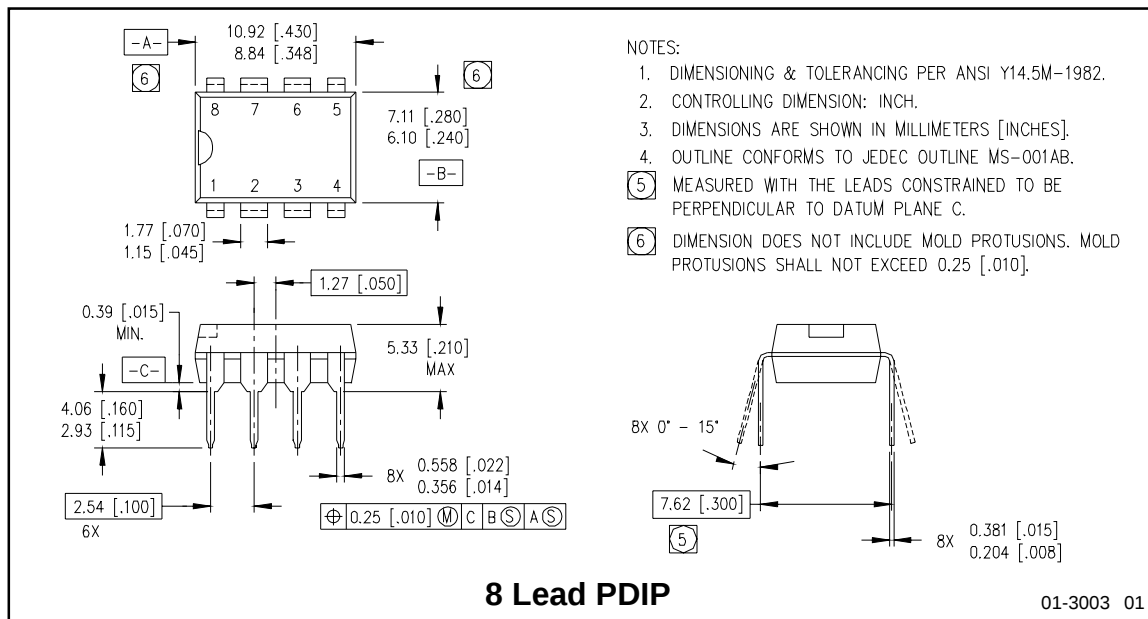
Lead Assignments

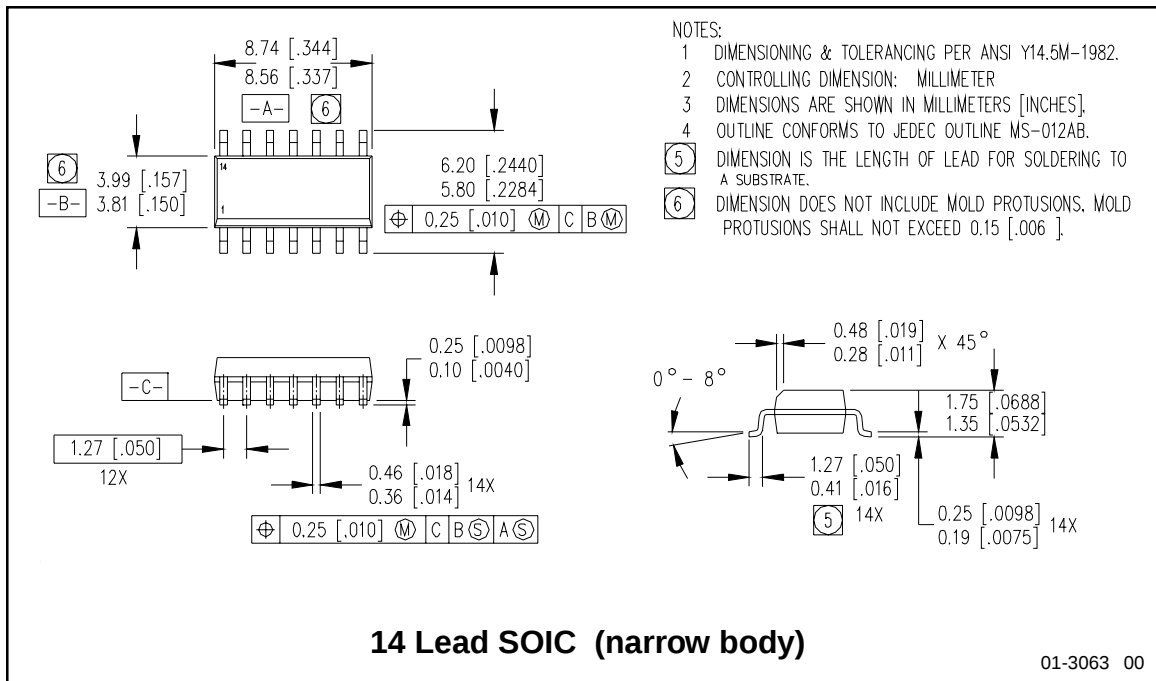
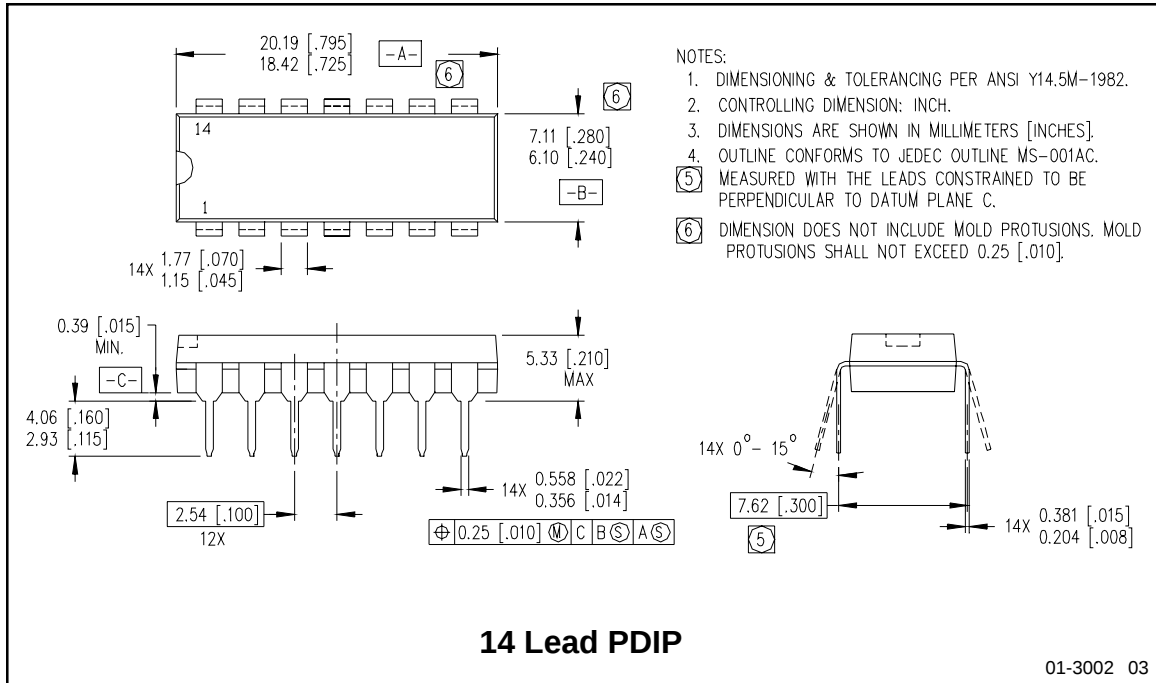
 8 Lead PDIP IR2184	 8 Lead SOIC IR2184S
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 14 Lead PDIP IR21844	 14 Lead SOIC IR21844S
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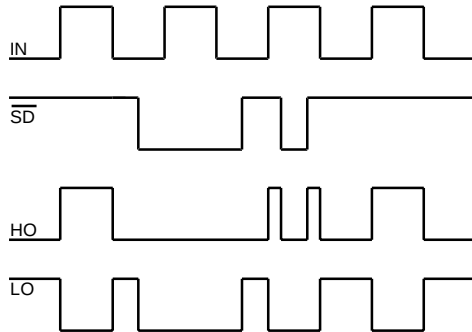


Figure 1. Input/Output Timing Diagram

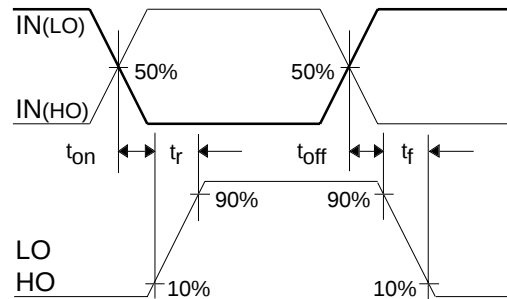


Figure 2. Switching Time Waveform Definitions

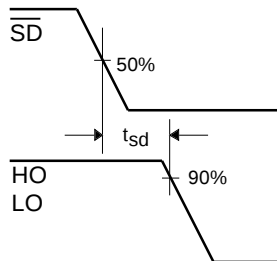


Figure 3. Shutdown Waveform Definitions

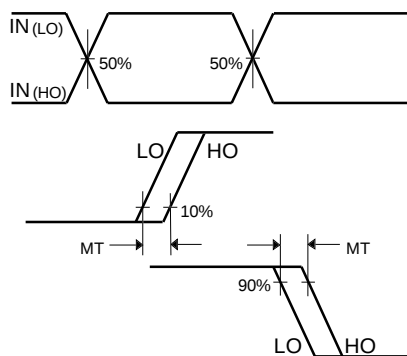


Figure 4. Deadtime Waveform Definitions

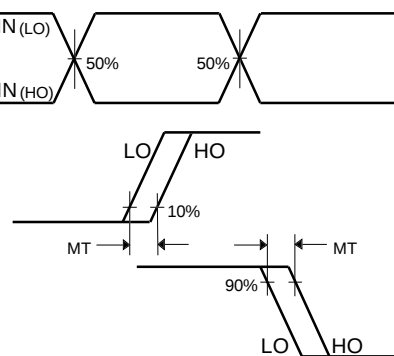


Figure 5. Delay Matching Waveform Definitions

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Data and specifications subject to change without notice. 4/12/2000

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